

## N-Channel 200V (D-S) MOSFET

PRODUCT SUMMARY		
$V_{DS}$ (V)	$R_{DS(on)}$ ( $\Omega$ )	$I_D$ (A)
200	0.056 at $V_{GS} = 10$ V	25
	0.070 at $V_{GS} = 6$ V	23

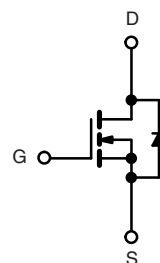
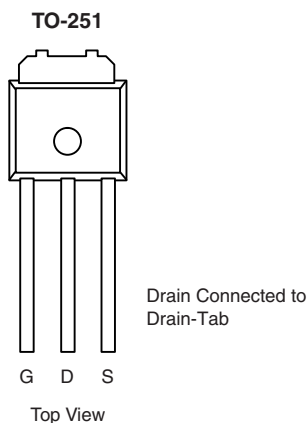
### FEATURES

- TrenchFET<sup>®</sup> Power MOSFET
- 175 °C Junction Temperature
- PWM Optimized
- 100 %  $R_g$  Tested
- Compliant to RoHS Directive 2002/95/EC



### APPLICATIONS

- Primary Side Switch



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS ( $T_A = 25$ °C, unless otherwise noted)				
Parameter		Symbol	Limit	Unit
Drain-Source Voltage		$V_{DS}$	200	V
Gate-Source Voltage		$V_{GS}$	$\pm 20$	
Continuous Drain Current ( $T_J = 175$ °C) <sup>b</sup>	$T_C = 25$ °C	$I_D$	25	A
	$T_C = 125$ °C		17	
Pulsed Drain Current		$I_{DM}$	60	
Continuous Source Current (Diode Conduction)		$I_S$	19	
Avalanche Current		$I_{AS}$	25	
Single Pulse Avalanche Energy	$L = 0.1$ mH	$E_{AS}$	18	mJ
Maximum Power Dissipation	$T_C = 25$ °C	$P_D$	145 <sup>b</sup>	W
	$T_A = 25$ °C		3.5 <sup>a</sup>	
Operating Junction and Storage Temperature Range		$T_J, T_{stg}$	- 55 to 175	°C

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Junction-to-Ambient <sup>a</sup>	$t \leq 10$ s	$R_{thJA}$	15	18	°C/W
	Steady State		40	50	
Junction-to-Case (Drain)		$R_{thJC}$	0.85	1.1	

Notes:

a. Surface mounted on 1" x 1" FR4 board.

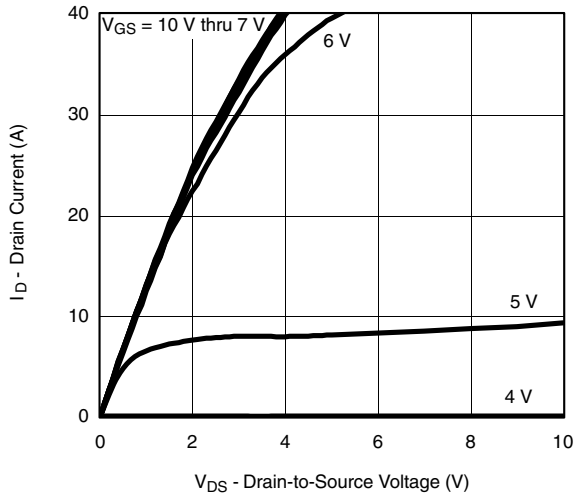
b. See SOA curve for voltage derating.

<b>SPECIFICATIONS</b> ( $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted)						
Parameter	Symbol	Test Conditions	Min.	Typ. <sup>a</sup>	Max.	Unit
<b>Static</b>						
Drain-Source Breakdown Voltage	$V_{DS}$	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	200			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	2		4	
Gate-Body Leakage	$I_{GSS}$	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 200\text{ V}, V_{GS} = 0\text{ V}$			1	$\mu\text{A}$
		$V_{DS} = 200\text{ V}, V_{GS} = 0\text{ V}, T_J = 125\text{ }^\circ\text{C}$			50	
		$V_{DS} = 200\text{ V}, V_{GS} = 0\text{ V}, T_J = 175\text{ }^\circ\text{C}$			250	
On-State Drain Current <sup>b</sup>	$I_{D(on)}$	$V_{DS} = 5\text{ V}, V_{GS} = 10\text{ V}$	40			A
Drain-Source On-State Resistance <sup>b</sup>	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 5\text{ A}$		0.056		$\Omega$
		$V_{GS} = 10\text{ V}, I_D = 5\text{ A}, T_J = 125\text{ }^\circ\text{C}$		0.130		
		$V_{GS} = 10\text{ V}, I_D = 5\text{ A}, T_J = 175\text{ }^\circ\text{C}$		0.260		
		$V_{GS} = 6\text{ V}, I_D = 5\text{ A}$		0.070		
Forward Transconductance <sup>b</sup>	$g_{fs}$	$V_{DS} = 15\text{ V}, I_D = 19\text{ A}$		35		S
<b>Dynamic<sup>a</sup></b>						
Input Capacitance	$C_{iss}$	$V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, F = 1\text{ MHz}$		2400		pF
Output Capacitance	$C_{oss}$			280		
Reverse Transfer Capacitance	$C_{rss}$			180		
Total Gate Charge <sup>c</sup>	$Q_g$	$V_{DS} = 100\text{ V}, V_{GS} = 10\text{ V}, I_D = 19\text{ A}$		40		nC
Gate-Source Charge <sup>c</sup>	$Q_{gs}$			10		
Gate-Drain Charge <sup>c</sup>	$Q_{gd}$			15		
Gate Resistance	$R_g$		0.5		2.9	$\Omega$
Turn-On Delay Time <sup>c</sup>	$t_{d(on)}$	$V_{DD} = 100\text{ V}, R_L = 5.2\text{ }\Omega$ $I_D \cong 19\text{ A}, V_{GEN} = 10\text{ V}, R_g = 2.5\text{ }\Omega$		15	25	ns
Rise Time <sup>c</sup>	$t_r$			50	75	
Turn-Off Delay Time <sup>c</sup>	$t_{d(off)}$			30	45	
Fall Time <sup>c</sup>	$t_f$			60	90	
<b>Source-Drain Diode Ratings and Characteristics</b> ( $T_C = 25\text{ }^\circ\text{C}$ )						
Pulsed Current	$I_{SM}$				50	A
Diode Forward Voltage <sup>b</sup>	$V_{SD}$	$I_F = 19\text{ A}, V_{GS} = 0\text{ V}$		0.9	1.5	V
Source-Drain Reverse Recovery Time	$t_{rr}$	$I_F = 19\text{ A}, di/dt = 100\text{ A}/\mu\text{s}$		180	250	ns

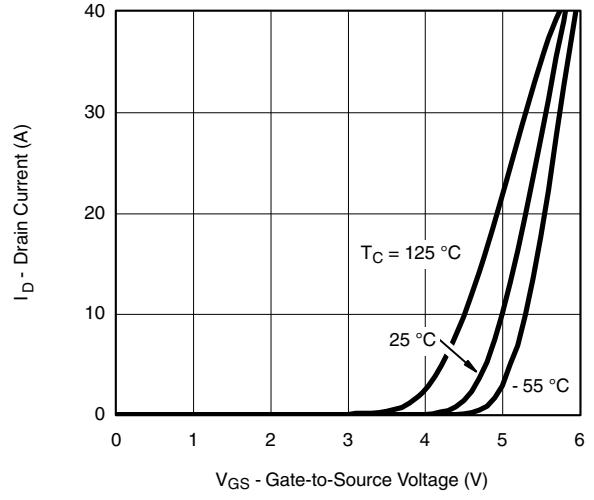
Notes:

- Guaranteed by design, not subject to production testing.
- Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$ .
- Independent of operating temperature.

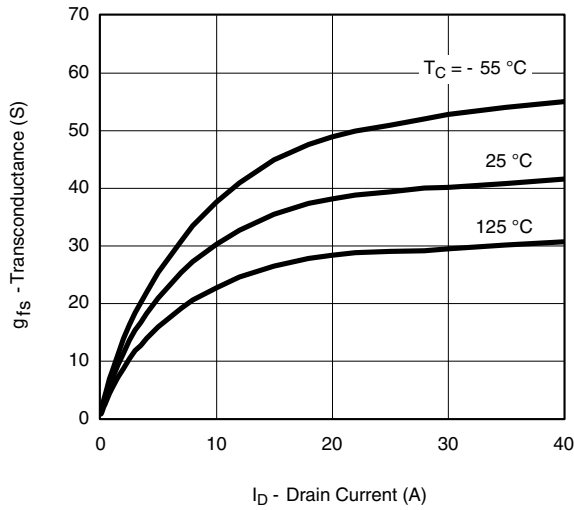
**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



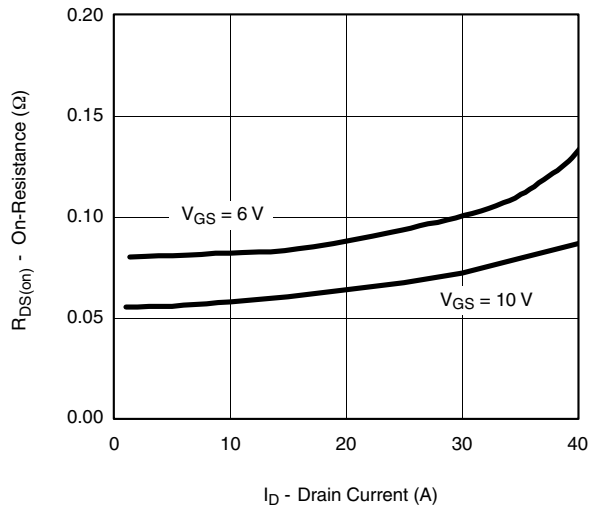
**Output Characteristics**



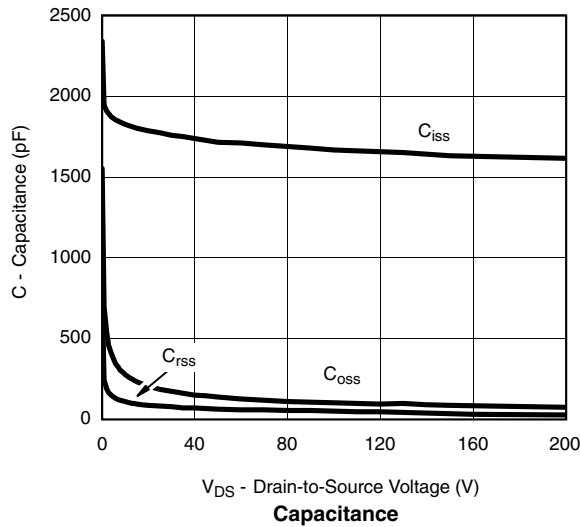
**Transfer Characteristics**



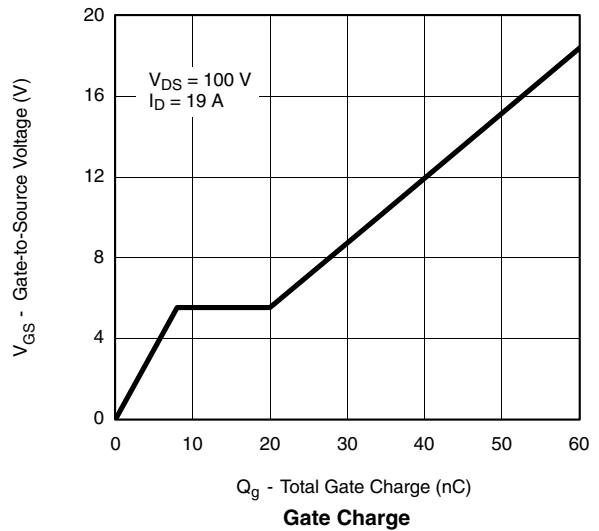
**Transconductance**



**On-Resistance vs. Drain Current**

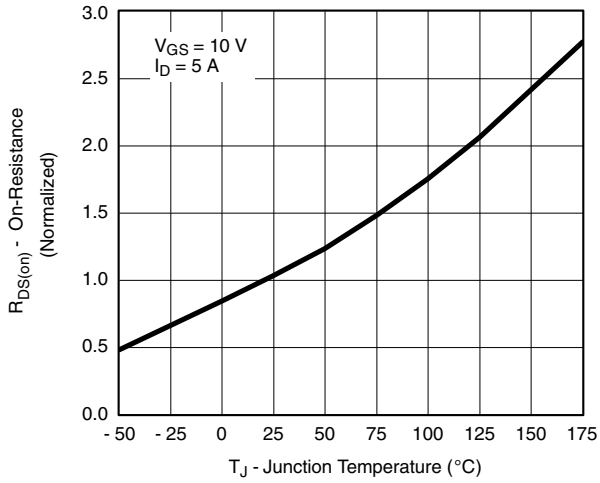


**Capacitance**

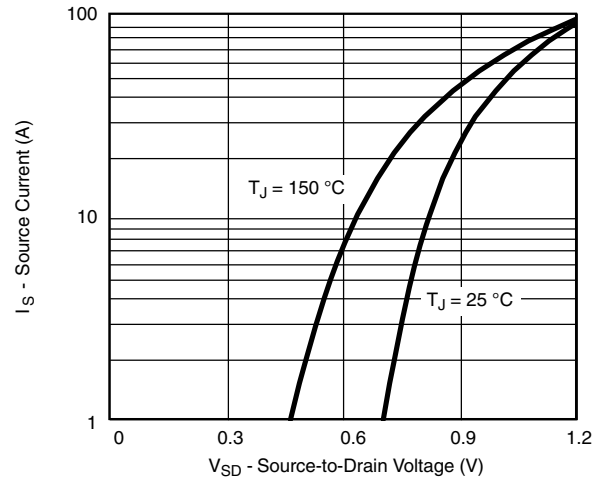


**Gate Charge**

**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)

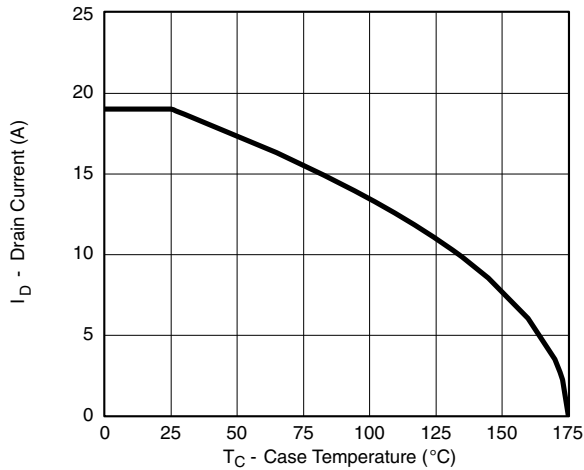


On-Resistance vs. Junction Temperature

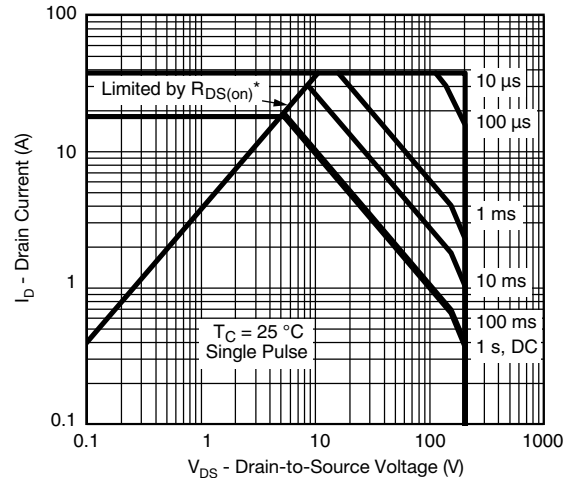


Source-Drain Diode Forward Voltage

**THERMAL RATINGS**

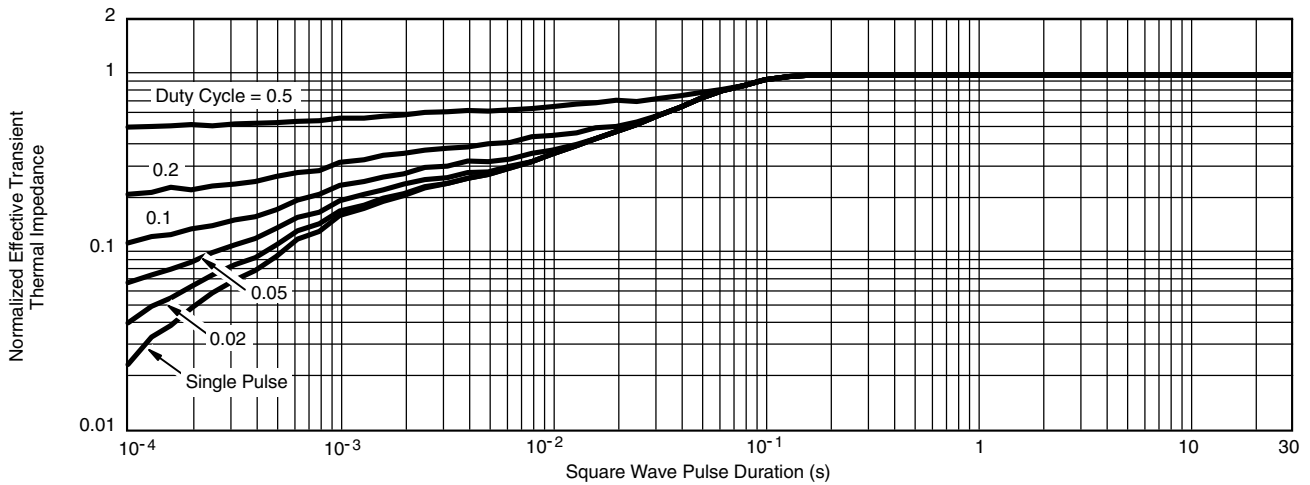


Maximum Avalanche Drain Current vs. Case Temperature



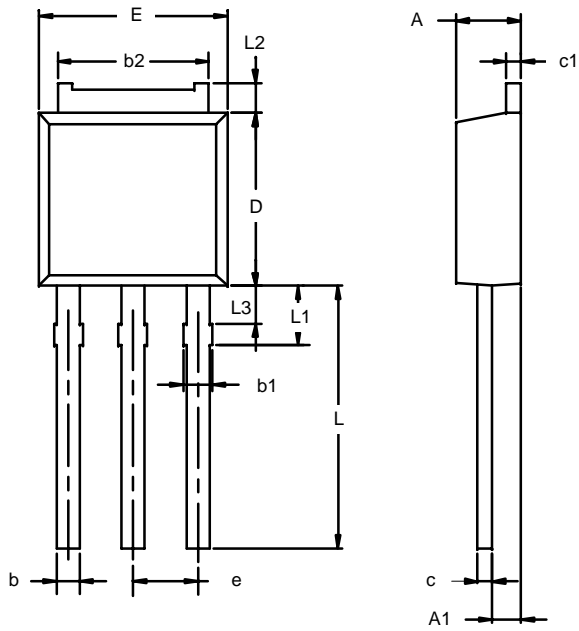
\*  $V_{GS} >$  minimum  $V_{GS}$  at which  $R_{DS(on)}$  is specified

Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Case

**TO-251AA**



Note: Dimension L3 is for reference only.

Dim	MILLIMETERS		INCHES	
	Min	Max	Min	Max
<b>A</b>	2.21	2.38	0.087	0.094
<b>A1</b>	0.89	1.14	0.035	0.045
<b>b</b>	0.71	0.89	0.028	0.035
<b>b1</b>	0.76	1.14	0.030	0.045
<b>b2</b>	5.23	5.43	0.206	0.214
<b>c</b>	0.46	0.58	0.018	0.023
<b>c1</b>	0.46	0.58	0.018	0.023
<b>D</b>	5.97	6.22	0.235	0.245
<b>E</b>	6.48	6.73	0.255	0.265
<b>e</b>	2.28 BSC		0.090 BSC	
<b>L</b>	3.89	9.53	0.153	0.375
<b>L1</b>	1.91	2.28	0.075	0.090
<b>L2</b>	0.89	1.27	0.035	0.050
<b>L3</b>	1.15	1.52	0.045	0.060

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